

N - CHANNEL ENHANCEMENT MODE FAST POWER MOS TRANSISTOR

PRELIMINARY DATA

TYPE	V _{DSS}	R _{DS(on)}	I _D
STY30NA50	500 V	< 0.175 Ω	30 A

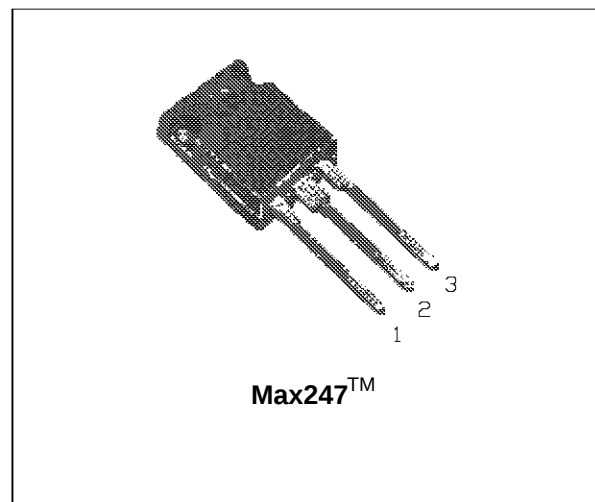
- TYPICAL R_{DS(on)} = 0.15 Ω
- EFFICIENT AND RELIABLE MOUNTING THROUGH CLIP
- ± 30V GATE TO SOURCE VOLTAGE RATING
- REPETITIVE AVALANCHE TESTED
- LOW INTRINSIC CAPACITANCE
- 100% AVALANCHE TESTED
- GATE CHARGE MINIMIZED
- REDUCED THRESHOLD VOLTAGE SPREAD

DESCRIPTION

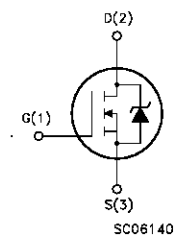
The Max247™ package is a new high volume power package exhibiting the same footprint as the industry standard TO-247, but designed to accommodate much larger silicon chips, normally supplied in bigger packages such as TO-264. The increased die capacity makes the device ideal to reduce component count in multiple paralleled designs and save board space with respect to larger packages.

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- DC-AC CONVERTERS FOR WELDING EQUIPMENT AND UNINTERRUPTIBLE POWER SUPPLIES (UPS)



INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	500	V
V _{DGR}	Drain- gate Voltage (R _{GS} = 20 kΩ)	500	V
V _{GS}	Gate-source Voltage	± 30	V
I _D	Drain Current (continuous) at T _c = 25 °C	30	A
I _D	Drain Current (continuous) at T _c = 100 °C	19	A
I _{DM} (•)	Drain Current (pulsed)	120	A
P _{tot}	Total Dissipation at T _c = 25 °C	300	W
	Derating Factor	2.4	W/°C
T _{stg}	Storage Temperature	-55 to 150	°C
T _j	Max. Operating Junction Temperature	150	°C

(•) Pulse width limited by safe operating area

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	0.42	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	40	°C/W
R _{thc-sink}	Thermal Resistance Case-Heatsink with Conductive Grease	Typ	0.05	

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max, δ < 1%)	30	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V)	3000	mJ
E _{AR}	Repetitive Avalanche Energy (pulse width limited by T _j max, δ < 1%)	180	mJ
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (T _c = 100 °C, pulse width limited by T _j max, δ < 1%)	19	A

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA V _{GS} = 0	500			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating x 0.8 T _c = 125 °C			200 1000	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 30 V			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 μA	2.25	3	3.75	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10 V I _D = 15 A V _{GS} = 10 V I _D = 15 A T _c = 100 °C		0.15	0.175 0.35	Ω Ω
I _{D(on)}	On State Drain Current	V _{DS} > I _{D(on)} x R _{DS(on)max} V _{GS} = 10 V	30			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} > I _{D(on)} x R _{DS(on)max} I _D = 15 A	25			S
C _{iss}	Input Capacitance	V _{DS} = 25 V f = 1 MHz V _{GS} = 0		6150	8000	pF
C _{oss}	Output Capacitance			780	1000	pF
C _{rss}	Reverse Transfer Capacitance			220	290	pF

ELECTRICAL CHARACTERISTICS (continued)**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Time Rise Time	$V_{DD} = 250\text{ V}$ $I_D = 15\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		40 70	55 90	ns ns
$(di/dt)_{on}$	Turn-on Current Slope	$V_{DD} = 400\text{ V}$ $I_D = 30\text{ A}$ $R_G = 47\ \Omega$ $V_{GS} = 10\text{ V}$		240		A/ μ s
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 400\text{ V}$ $I_D = 30\text{ A}$ $V_{GS} = 10\text{ V}$		245 27 120	320	nC nC nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$ t_f t_c	Off-voltage Rise Time Fall Time Cross-over Time	$V_{DD} = 400\text{ V}$ $I_D = 30\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		75 30 110	100 40 145	ns ns ns

SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM}(\bullet)$	Source-drain Current Source-drain Current (pulsed)				30 120	A A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 30\text{ A}$ $V_{GS} = 0$			1.6	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 30\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$		800 17.6 44		ns μ C A

(*) Pulsed: Pulse duration = 300 μ s, duty cycle 1.5 %

(\bullet) Pulse width limited by safe operating area

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